

# RRL025P03FRA

# Pch -30V -2.5A Power MOSFET

$V_{DSS}$	-30V
R <sub>DS(on)</sub> (Max.)	75m $Ω$
I <sub>D</sub>	-2.5A
$P_{D}$	1.0W

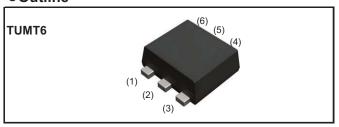
#### Features

- 1) Low on resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TUMT6).
- 4) Pb-free lead plating; RoHS compliant
- 5) AEC-Q101 Qualified

# Application

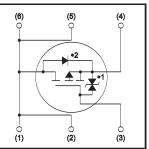
DC/DC converters

#### Outline



### •Inner circuit

- (1) Drain (2) Drain
- (3) Gate
- (4) Source
- (5) Drain
- (6) Drain
- \*1 ESD PROTECTION DIODE
- \*2 BODY DIODE



Packaging specifications

	Packaging	Taping
	Reel size (mm)	180
Tuno	Tape width (mm)	8
Туре	Basic ordering unit (pcs)	3,000
	Taping code	TR
	Marking	UA

# ● Absolute maximum ratings(T<sub>a</sub> = 25°C)

Parameter	Symbol	Value	Unit
Drain - Source voltage	$V_{ extsf{DSS}}$	-30	V
Continuous drain current	I <sub>D</sub> *1	±2.5	А
Pulsed drain current	I <sub>D,pulse</sub> *2	±10	А
Gate - Source voltage	$V_{GSS}$	±20	V
Dower discination	P <sub>D</sub> *3	1.0	W
Power dissipation	P <sub>D</sub> *4	0.32	W
Junction temperature	T <sub>j</sub>	150	°C
Range of storage temperature	T <sub>stg</sub>	-55 to +150	°C

# ●Thermal resistance

Parameter	Symbol	Values			Unit
Farameter		Min.	Тур.	Max.	Offic
Thermal resistance, junction - ambient	R <sub>thJA</sub> *3	-	-	125	°C/W
	R <sub>thJA</sub> *4	-	-	391	°C/W

# ●Electrical characteristics(T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = -1mA$	-30	-	-	V	
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$	I <sub>D</sub> = -1mA referenced to 25°C	1	-25	,	mV/°C	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = -30V, V_{GS} = 0V$	1	-	-1	μА	
Gate - Source leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±10	μА	
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS} = -10V, I_{D} = -1mA$	-1	-	-2.5	V	
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_{j}}$	I <sub>D</sub> = -1mA referenced to 25°C	-	3.9	-	mV/°C	
		$V_{GS} = -10V, I_D = -2.5A$	-	55	75		
Static drain - source	D *5	$V_{GS} = -4.5V, I_D = -1.2A$	-	85	115		
on - state resistance	$R_{DS(on)}$	$V_{GS} = -4.0V, I_D = -1.2A$	-	95	125	mΩ	
		V <sub>GS</sub> = -10V, I <sub>D</sub> = -2.5A, T <sub>j</sub> =125°C	-	95	135		
Gate input resistannce	$R_G$	f = 1MHz, open drain	-	24	-	Ω	
Transconductance	<b>g</b> fs *5	$V_{DS} = -10V, I_{D} = -2.5A$	2.0	4.4	-	S	

<sup>\*1</sup> Limited only by maximum temperature allowed.

<sup>\*2</sup> Pw  $\leq 10 \mu s, \, Duty \, cycle \leq 1\%$ 

<sup>\*3</sup> Mounted on a seramic board (30×30×0.8mm)

<sup>\*4</sup> Mounted on a FR4 (15×20×0.8mm)

<sup>\*5</sup> Pulsed

# ●Electrical characteristics(T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	480	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -10V	-	70	-	pF
Reverse transfer capacitance	$C_{rss}$	f = 1MHz	-	70	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \simeq -15V$ , $V_{GS} = -10V$	-	7	-	
Rise time	t <sub>r</sub> *5	I <sub>D</sub> = -1.2A	-	16	-	no
Turn - off delay time	${\rm t_{d(off)}}^{*5}$	$R_L = 12.5\Omega$	-	50	-	ns
Fall time	t <sub>f</sub> *5	$R_G = 10\Omega$	-	33	-	

# •Gate Charge characteristics( $T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	+-	$V_{DD} \simeq -15V, I_{D} = -2.5A$ $V_{GS} = -5V$	-	5.2	-	
Total gate charge	Q <sub>g</sub> *5	$V_{DD} \simeq -15V, I_D = -2.5A$ $V_{GS} = -10V$	1	12	-	nC
Gate - Source charge	Q <sub>gs</sub> *5	$V_{DD} \simeq -15V, I_D = -2.5A$ $V_{GS} = -5V$	-	1.6	-	
Gate - Drain charge	Q <sub>gd</sub> *5	$V_{GS} = -5V$	-	1.6	-	

# ●Body diode electrical characteristics (Source-Drain)(T<sub>a</sub> = 25°C)

Parameter	Symbol Conditions		Values			Unit
r ai ai ii etei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l <sub>S</sub> *1	T <sub>a</sub> = 25°C	-	-	-0.8	А
Forward voltage	V <sub>SD</sub> *5	$V_{GS} = 0V, I_s = -2.5A$	-	-	-1.2	V

# •Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

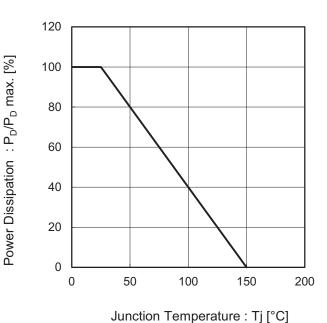
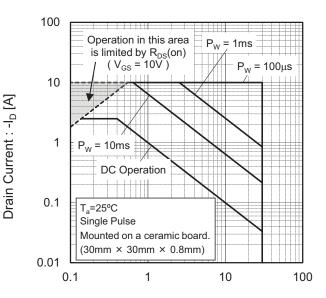
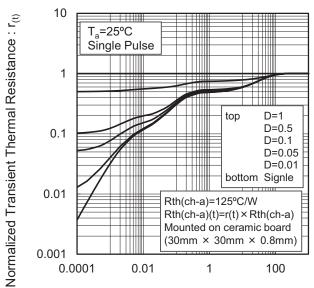


Fig.2 Maximum Safe Operating Area



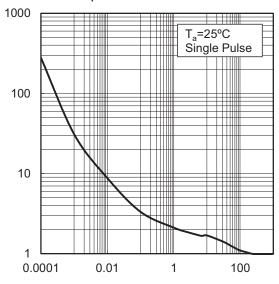
Drain - Source Voltage : -V<sub>DS</sub> [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Pulse Width : P<sub>W</sub> [s]

Fig.4 Single Pulse Maxmum Power dissipation



Pulse Width: P<sub>W</sub> [s]

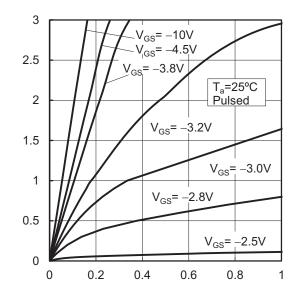
Peak Transient Power: P(W)

Drain Current: -I<sub>D</sub> [A]

Drain - Source Breakdown Voltage : - $V_{(BR)DSS}$  [V]

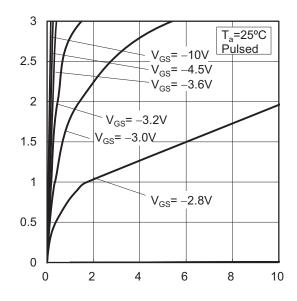
### •Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)



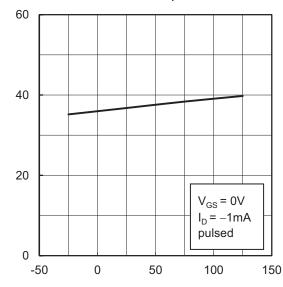
Drain - Source Voltage : -V<sub>DS</sub> [V]

Fig.6 Typical Output Characteristics(II)



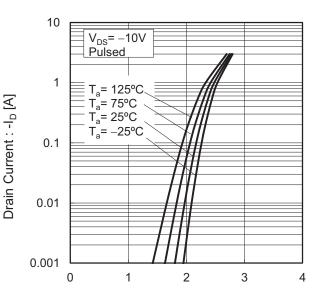
Drain - Source Voltage : -V<sub>DS</sub> [V]

Fig.7 Breakdown Voltage vs. Junction Temperature



Junction Temperature :  $T_j$  [°C]

Fig.8 Typical Transfer Characteristics



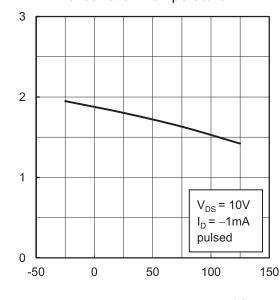
Gate - Source Voltage : -V<sub>GS</sub> [V]

Drain Current: -I<sub>D</sub> [A]

Gate Threshold Voltage: -VGS(th) [V]

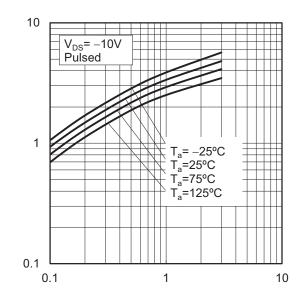
# •Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs. Junction Temperature



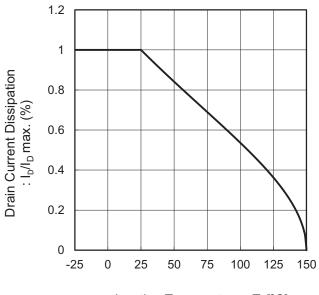
Junction Temperature : T<sub>i</sub> [°C]

Fig.10 Transconductance vs. Drain Current



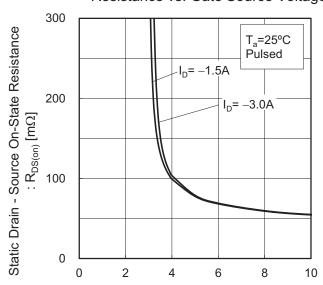
Drain Current: -ID [A]

Fig.11 Drain CurrentDerating Curve



Junction Temperature : T<sub>i</sub> [°C]

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

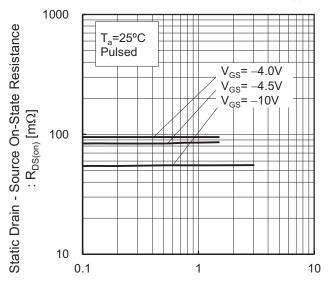


Gate - Source Voltage : -V<sub>GS</sub> [V]

Transconductance: gfs [S]

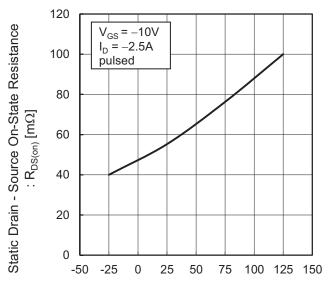
#### • Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)



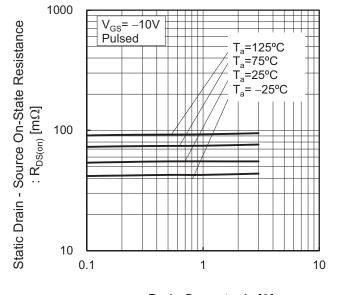
Drain Current: -ID [A]

Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



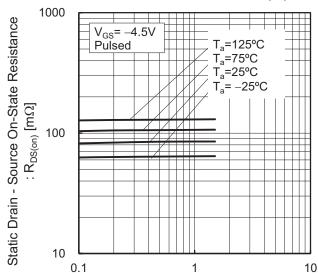
Junction Temperature : T<sub>i</sub> [°C]

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)



Drain Current :  $-I_D$  [A]

Fig.16 Static Drain-Source On-State Resistance vs. Drain Current(III)



Drain Current : -I<sub>D</sub> [A]

### • Electrical characteristic curves

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV) 1000 Static Drain - Source On-State Resistance  $V_{GS} = -4.0V$ Pulsed T<sub>a</sub>=75°C T<sub>a</sub>=25°C  $T_a = -25^{\circ}C$  $:R_{DS(on)}\left[ m\Omega \right]$ 100 10 0.1 1 10 Drain Current: -ID [A]

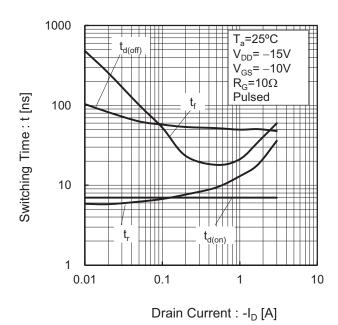
Fig.18 Typical Capacitance
vs. Drain - Source Voltage

1000

Coss
Ciss
Ciss
Ta=25°C
f=1MHz
VGS=0V

Drain - Source Voltage : -VDS [V]

Fig.19 Switching Characteristics



Gate - Source Voltage : -V<sub>GS</sub> [V]

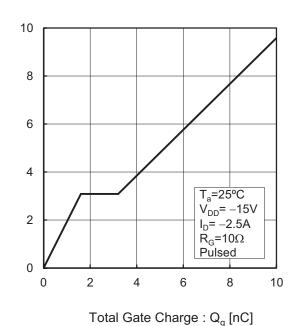
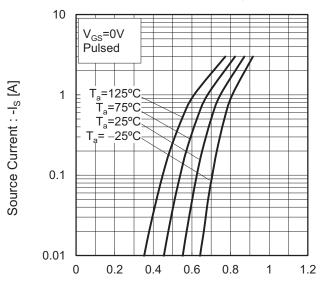


Fig.20 Dynamic Input Characteristics

# •Electrical characteristic curves

Fig.21 Source Current vs. Source Drain Voltage



Source-Drain Voltage : - $V_{SD}$  [V]

# Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

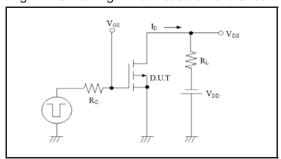


Fig.2-1 Gate Charge Measurement Circuit

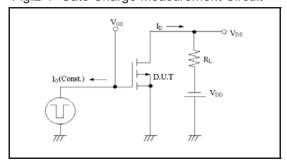


Fig.1-2 Switching Waveforms

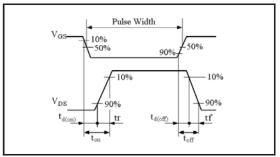
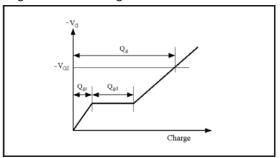
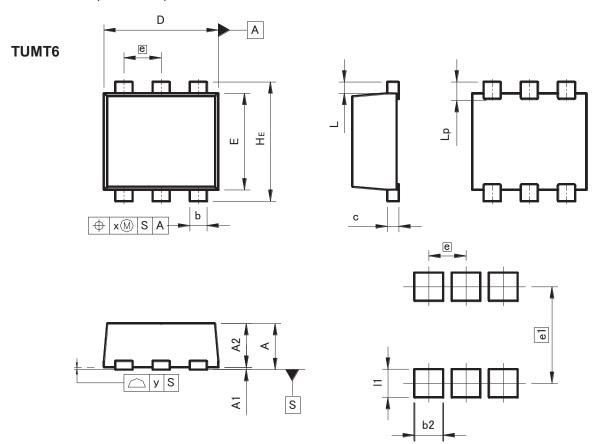


Fig.2-2 Gate Charge Waveform



# ●Dimensions (Unit : mm)



Patterm of terminal position areas

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	ı	0.85	ı	0.033	
A1	0.00	0.10	0	0.004	
A2	0.72	0.82	0.028	0.032	
b	0.25	0.40	0.01	0.016	
С	0.12	0.22	0.005	0.009	
D	1.90	2.10	0.075	0.083	
E	1.60	1.80	0.063	0.071	
е	0.0	65	0.0	03	
HE	2.00	2.20	0.079	0.087	
L	0.5	20	0.0	01	
Lp	_	0.40	_	0.016	
Х	_	0.10	_	0.004	
У	_	0.10	_	0.004	

DIM MILI		ETERS	INCHES	
ואונט	MIN	MAX	MIN	MAX
e1	1.70		0.067	
b2	_	0.50	_	0.02
l1	_	0.50	-	0.02

Dimension in mm/inches

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JAPAN	USA	EU	CHINA
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  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
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- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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